SEMICONDUCTOR

TECHNICAL DATA
DATA SHEET 4842,REV.-

Green Products

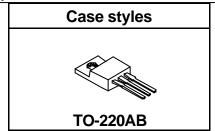
FEP16AT-G-FEP16JT-G ULTRAFAST PLASTIC RECTIFIER

Mechanical Data

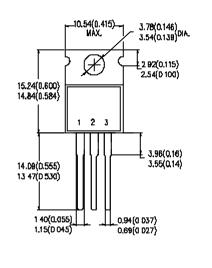
- Case: JEDEC TO-220AB molded plastic body over passivated chips
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026
- Polarity: As markedMounting Position: Any
- Mounting Torque: 5 in. Ibs. max.
- · Weight: 0.08 ounce, 2.24 grams

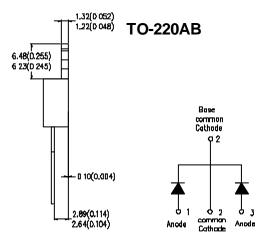
Features:

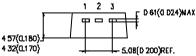
- Low forward voltage drop
- High surge current capacity
- High current capability
- High reliability
- Superfast recovery times for high efficiency
- Dual rectifier construction, positive centertap
- Green Products in Compliance with the RoHS Directive



Mechanical Dimensions: In Inches / mm







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Maximum Ratings and Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise noted.

Parameter	Symbol	FEP 16AT-G	FEP 16BT-G	FEP 16CT-G	FEP 16DT-G	FEP 16FT-G	FEP 16GT-G	FEP 16HT-G	FEP 16JT-G	Unit
Maximum repetitive peak reverse voltage	VRRM	50	100	150	200	300	400	500	600	V
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	350	420	V
Maximum DC blocking voltage	VDC	50	100	150	200	300	400	500	600	V
Maximum average forward rectified current at TC = 100°C	I _{F(AV)}	16							А	
Peak forward surge current 8.3 ms single halfsine wave superimposed on rated load (JEDEC method)	IFSM	200							А	
Typical thermal reisistance (NOTE 3)	R _Θ JA R _Θ JC	15.0 2.2							°C/W	
Operating junction and storage temperature range	TJ, TSTG	-55 to +150							°C/W	

Electrical Characteristics

Parameter	Symbol	FEP 16AT-G	FEP 16BT-G	FEP 16CT-G	FEP 16DT-G	FEP 16FT-G	FEP 16GT-G	FEP 16HT-G	FEP 16JT-G	Unit
Maximum instantaneous forward voltage per leg at 8.0 A	VF	0.95			1.3		1.5		V	
Maximum DC reverse current at rated DC blocking voltage per leg $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	l _R	10 500							μА	
Maximum reverse recovery time per leg (NOTE 1)	t _{rr}	35 50					ns			
Typical junction capacitance per leg (NOTE 2)	CJ	85.0				6	0	pF		

NOTES: (1) Reverse recovery test conditions: $I_F = 0.5 \text{ A}$, $I_R = 1.0 \text{ A}$, $I_{R} = 0.25 \text{ A}$

⁽²⁾ Measured at 1.0 MHz and applied reverse voltage of 4.0 V
(3) Thermal resistance from junction to ambient and from junction to case per leg mounted on heatsink

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Figure 1. Forward Current Derating Curve

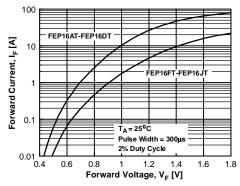


Figure 3. Forward Voltage Characteristics

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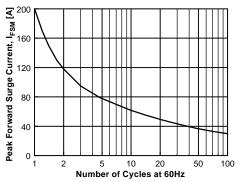


Figure 2. Non-Repetitive Surge Current Reverse Characteristics

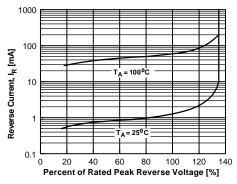
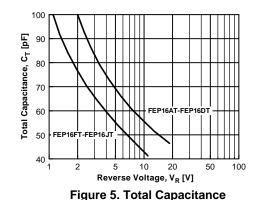


Figure 4. Reverse Current vs Reverse Voltage



50Ω NONINDUCTIVE

50Ω NONINDUCTIVE

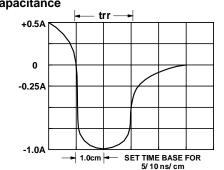
DUT

Pulse Generator (Note 2)

50Ω NONINDUCTIVE

(+)

OSCILLOSCOPE (Note 1)



Reverse Recovery Time Characterstic and Test Circuit Diagram

[•] World Wide Web Site - http://www.sensitron.com • E-Mail Address - sales@sensitron.com •

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